



MMC 4070 MMC 4077

QUAD EXCLUSIVE-OR GATE 4070 QUAD EXCLUSIVE-NOR GATE 4077

GENERAL DESCRIPTION

The MMC 4070/4077 are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package.

The MMC 4070 contains four independent exclusive-OR gates.

The MMC 4077 contains four independent exclusive-NOR gates.

The MMC 4070 and MMC 4077 provide the system designer with a means for direct implementation of exclusive-OR and exclusive-NOR function, respectively.

FEATURES

- Medium-speed operation $t_{PHL} = t_{PLH} = 65$ ns (TYP.) at $V_{DD} = 10$ V, $C_L = 50$ pF
- 100% tested for quiescent current

APPLICATIONS

- Logical comparators
- Adders/subtractors
- Parity generators and checkers

ABSOLUTE MAXIMUM RATINGS

V_{DD}^*	Supply voltage: G and H types	-0.5 to 20	V
	E and F types	-0.5 to 18	V
V_i	Input voltage	-0.5 to $V_{DD}+0.5$	V
I_i	DC input current (any one input)	± 10	mA
P_{tot}	Total power dissipation (per package)	200	mW
	Dissipation per output transistor for $T_A =$ full package-temperature range	100	mW
T_A	Operating temperature: G and H types	-55 to 125	°C
	E and F types	-40 to 85	°C
T_{stg}	Storage temperature	-65 to 150	°C

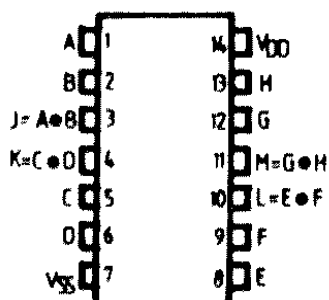
* All voltage values are referred to V_{SS} pin voltage

RECOMMENDED OPERATING CONDITIONS

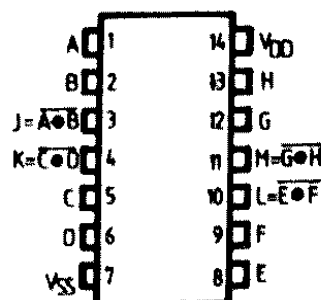
V_{DD}^*	Supply voltage: G and H types	3 to 18	V
	E and F types	3 to 15	V
V_i	Input voltage	0 to V_{DD}	V
T_A	Operating temperature: G and H types	-55 to 125	°C
	E and F types	-40 to 85	°C

CONNECTION DIAGRAMS

MMC 4070



MMC 4077



STATIC ELECTRICAL CHARACTERISTICS

(over recommended operating conditions)

PARAMETER			TEST CONDITIONS				VALUES						UNI	
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{LOW} *		25°C			T _{HIGH} *		
							min.	max.	min.	typ	max.	min.		max.
I _L	Quiescent current	G, H types	0/5			5		1	0.02	1		30	μ A	
			0/10			10		2	0.02	2		60		
			0/15			15		4	0.02	4		120		
			0/20			20		20	0.04	20		600		
	E, F types	0/5			5		4	0.02	4		30			
		0/10			10		8	0.02	8		60			
			0/15			15		0.02	16		120			
V _{OH}	Output high voltage		0/5		< 1	5	4.95		4.95		4.95	V		
			0/10		< 1	10	9.95		9.95		9.95			
			0/15		< 1	15	14.95		14.95		14.95			
V _{OL}	Output low voltage		5/0		< 1	5		0.05		0.05	0.05	V		
			10/0		< 1	10		0.05		0.05	0.05			
			15/0		< 1	15		0.05		0.05	0.05			
V _{IH}	Input high voltage			0.5/4.5	< 1	5	3.5		3.5		3.5	V		
				1/9	< 1	10	7		7		7			
				1.5/13.5	< 1	15	11		11		11			
V _{IL}	Input low voltage			4.5/0.5	< 1	5		1.5		1.5	1.5	V		
				9/1	< 1	10		3		3	3			
				13.5/1.5	< 1	15		4		4	4			
I _{OH}	Output drive current	G, H types	0/5	2.5		5	-2		-1.6	-3.2		-1.15	mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		E, F types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
		0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
		0/15	13.5		15	-3.6		-3.0	-6.8		-2.4			
I _{OL}	Output sink current	G, H types	0/5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		E, F types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} I _{IL}	Input leakage current	G, H types	0/18	Any input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		E, F types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
C _I	Input capacitance			Any input					5	7.5			pF	

* T_{LOW} = -55°C for G, H devices; -40°C for E, F devices.* T_{HIGH} = +125°C for G, H devices; +85°C for E, F devices.

The Noise Margin for both "1" and "0" level is:

1 V min. with V_{DD} = 5 V2 V min. with V_{DD} = 10 V2.5 V min. with V_{DD} = 15 V

DYNAMIC ELECTRICAL CHARACTERISTICS

$T_c = 25^\circ\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^\circ\text{C}$, all input rise and fall times = 20 ns

PARAMETER	TEST CONDITIONS		VALUES			UNIT
		$V_{CC}(V)$	MIN.	TYP.	MAX.	
t_{PHL} Propagation delay time		5		140	280	ns
		10		65	130	
		15		50	100	
t_{TLH} Transition time		5		100	200	ns
		10		50	100	
		15		40	80	

TRUTH TABLE

(of 4 gates)

4070

A	B	J
0	0	0
1	0	1
0	1	1
1	1	0

here 1 = High level
0 = Low level
J = $A \oplus B$

4077

A	B	J
0	0	1
1	0	0
0	1	0
1	1	1

here 1 = High level
0 = Low level
J = $A \ominus B$

FUNCTIONAL DIAGRAM

